



Resistive Effects in Ceramic Kicker Chamber. Roughness Effects in Undulator Chamber.

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DESY, 16 April 2007

Topics

- Impedance Structure Investigation for Ceramic Kicker Vacuum Chamber with metallic coats.
- Resistive and Geometrical Wakes.
- Influence of Surface Roughness in Undulator Chamber on the Beam.

Impedance Structure Investigation of Ceramic Kicker Vacuum Chamber with Metallic Coats.

Longitudinal Impedance. Monopole term.



$$Z(k) = -\frac{jZ_0}{\pi k U}$$

$$U = a_2^2 - 2 \frac{a_2 \epsilon_3}{\chi_3 \epsilon_0} \times \frac{\epsilon_3 \chi_4 R_4(a_3) S'_3(a_2) - \epsilon_4 \chi_3 R'_3(a_2) R_4'(a_3)}{\epsilon_3 \chi_4 R_4(a_3) S_3(a_2) - \epsilon_4 \chi_3 R_3(a_2) R_4'(a_3)}$$

R, R', S, S' - combination of Bessel functions.

Single layer cylindrical tube

$$U = a^2 - 2 \frac{a \epsilon}{\epsilon_0 \chi} \frac{K_0(\chi b) I_1(\chi a) + I_0(\chi b) K_1(\chi a)}{K_0(\chi b) I_0(\chi a) - I_0(\chi b) K_0(\chi a)}$$

Metallic type layers

$$\varepsilon_i = \varepsilon_0 - j\sigma_i/\omega \quad \chi_i = \sqrt{j\mu_0\sigma_i\omega}$$

Good approximation - the smallness of each layer skin depth with respect to the layer inner radius $\delta_i / a_i \ll 1$

$$U = a^2 - 2 \frac{a\varepsilon_3}{\varepsilon_0\chi_3} \times \frac{1 + \alpha th\chi_3 d_3 th\chi_4 d_4}{th\chi_3 d_3 + \alpha th\chi_4 d_4}$$

$$|a_2\chi_3| \gg 1$$
$$\alpha \approx (\sigma_3/\sigma_4)^{1/2}$$

Single layer tube $\alpha = 1$

$$U = a^2 - 2 \frac{a\varepsilon}{\varepsilon_0\chi} cth\chi d$$

Ceramic type layers with metallic coats

Good approximation:

$$|a_2\chi_3| \gg 1$$

Metallic layer

$$\epsilon_3 = \epsilon_0 - j \frac{\sigma}{ck}$$

$$\chi_3 = \sqrt{jc\mu_0\sigma k}$$

$$|a_3\chi_4| \gg 1$$

Ceramic layer

$$\epsilon_4 = \epsilon_0 n^2$$

$$\chi_4 = jk\sqrt{n^2 - 1}$$

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$$U = a^2 + 2 \frac{a\epsilon_3}{\epsilon_0\chi_3} \times \frac{1 - j\alpha \operatorname{th}(\chi_3 d_3) \operatorname{th}(kn'd_4)}{\operatorname{th}(\chi_3 d_3) - j\alpha \operatorname{th}(kn'd_4)}$$

$$n' = \sqrt{n^2 - 1}$$

$$\alpha = \frac{\chi_4}{\chi_3} \frac{\epsilon_3}{\epsilon_4}$$

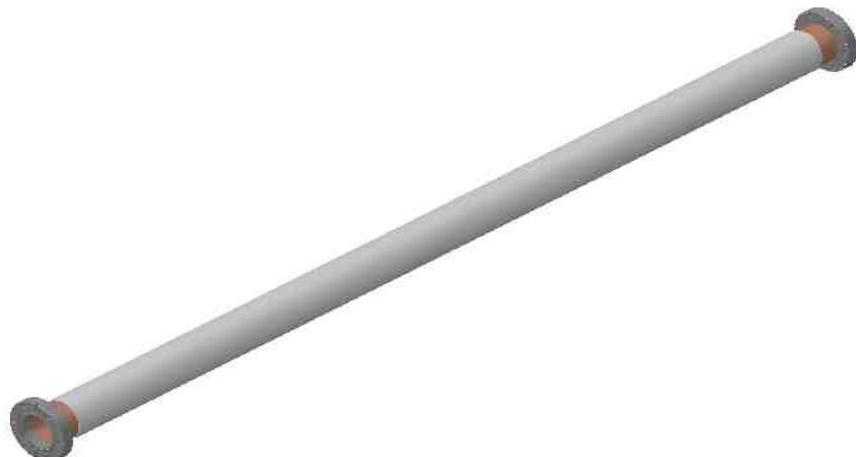
$$U = a^2 + 2 \frac{a\epsilon_3}{\epsilon_0\chi_3} \operatorname{cth}(\chi_3 d_3) \quad kn'd_4 = \pi l \quad l \in N$$

$$U = a^2 + 2 \frac{a\epsilon_3}{\epsilon_0\chi_3} \operatorname{th}(\chi_3 d_3) \quad kn'd_4 = \frac{\pi}{2} + \pi l$$

Actually for all the practical applications, the formula () is valid and well approximates the exact solution.*

Numerical Examples

Ceramic Kicker Vacuum chamber:
Ceramic with Titanium-Stabilized High Gradient Steel (TSHGS) coats



Vacuum Chamber Parameters

Radius - 0.01 m

Length - 0.9 m

TSHGS Parameters



Thickness - $0.7 \mu\text{m}$

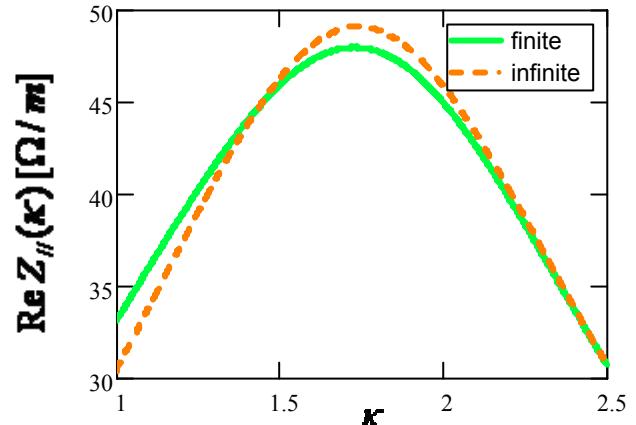
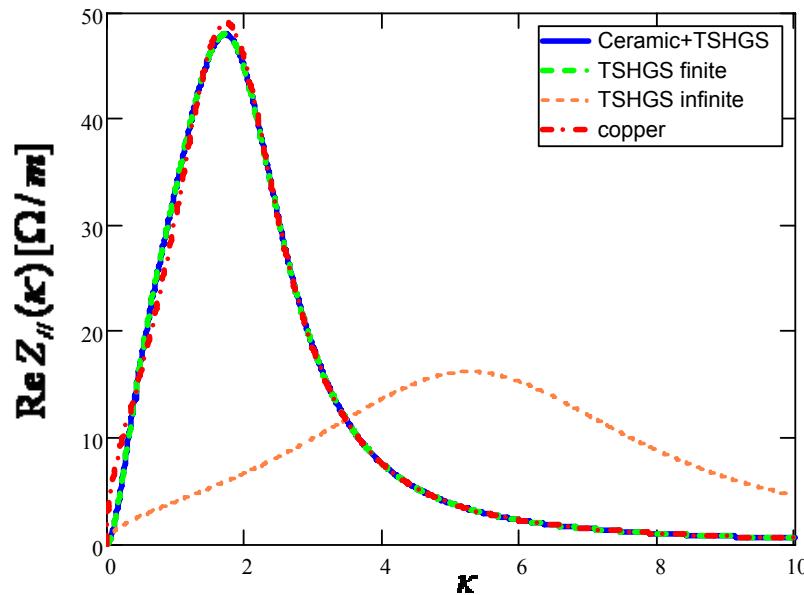
Resistance - $R/L = 10 - 12 \Omega\text{m}^{-1}$

$$\sigma \approx (2.0841 \pm 0.18946) \times 10^6 \Omega^{-1}\text{m}^{-1}$$

Parameters from T. Wohlenberg

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Longitudinal Impedance Per Unit Length. Monopole term.

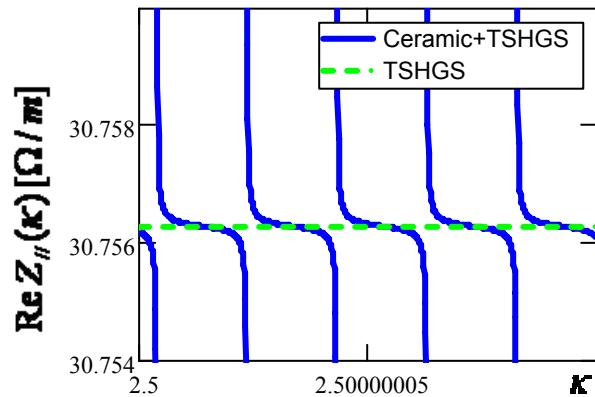


Longitudinal monopole impedance as function of dimensionless wave number $\kappa = k \cdot s_0$ for several cases of vacuum chamber material:

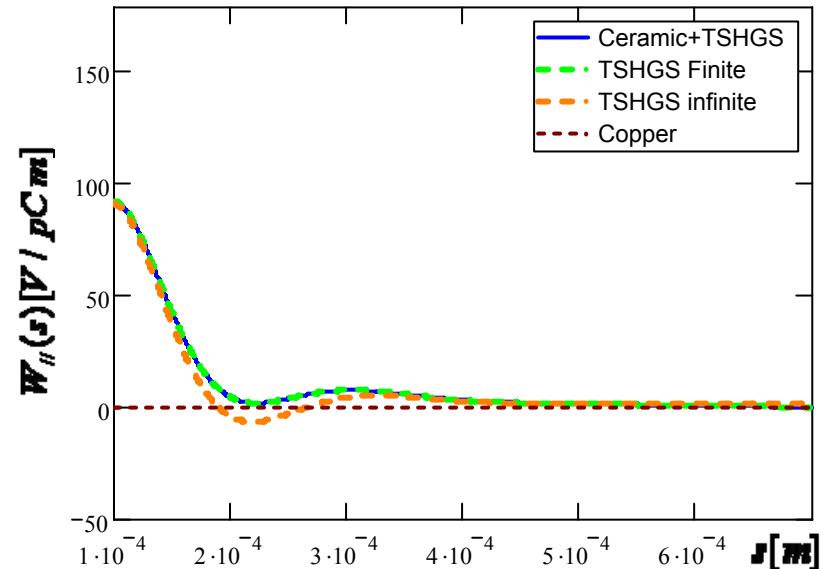
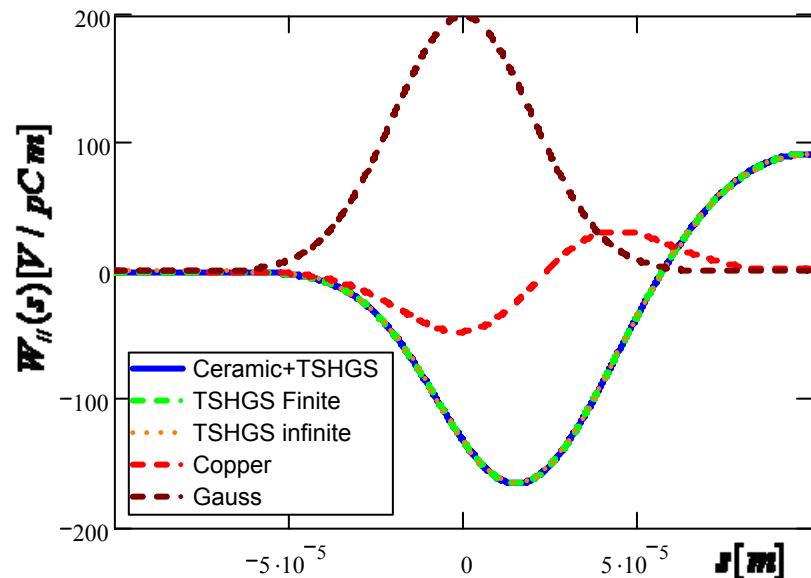
1. Ceramic with TSHGS coats.
2. TSHGS single layer tube with finite and infinite thickness.
3. Copper single layer tube.

$$\kappa = ks_0$$

$$\textbf{s}_0 \text{ characteristic distance: } s_0 = (2ca^2\epsilon_0 / \sigma)^{1/3} \approx 63.4 \mu\text{m}$$



Resistive Wall Wakes



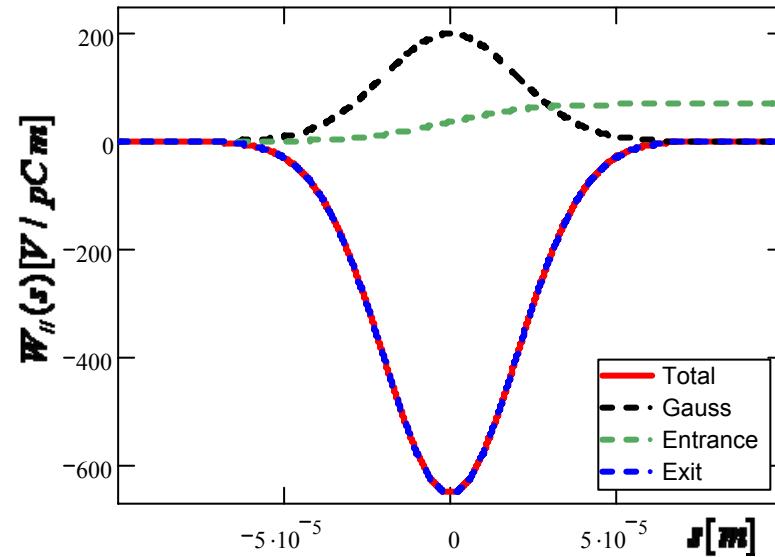
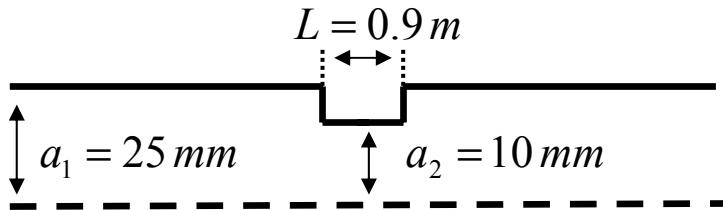
Resistive wall longitudinal wake potentials of Gaussian bunch with $\sigma_b = 20 \mu\text{m}$ for several cases of vacuum chamber material:

1. Ceramic with TSHGS coats.
2. TSHGS single layer tube with finite and infinite thickness.
3. Copper single layer tube.

$$E = 17.5 \text{ GeV}$$

	Ceramic+TSHGS	TSHGS	Copper
Loss Factor[kV / nC]	-108.43	-108.4	-26.29
Energy Spread [%]	0.288	0.288	0.12

Geometrical Wakes

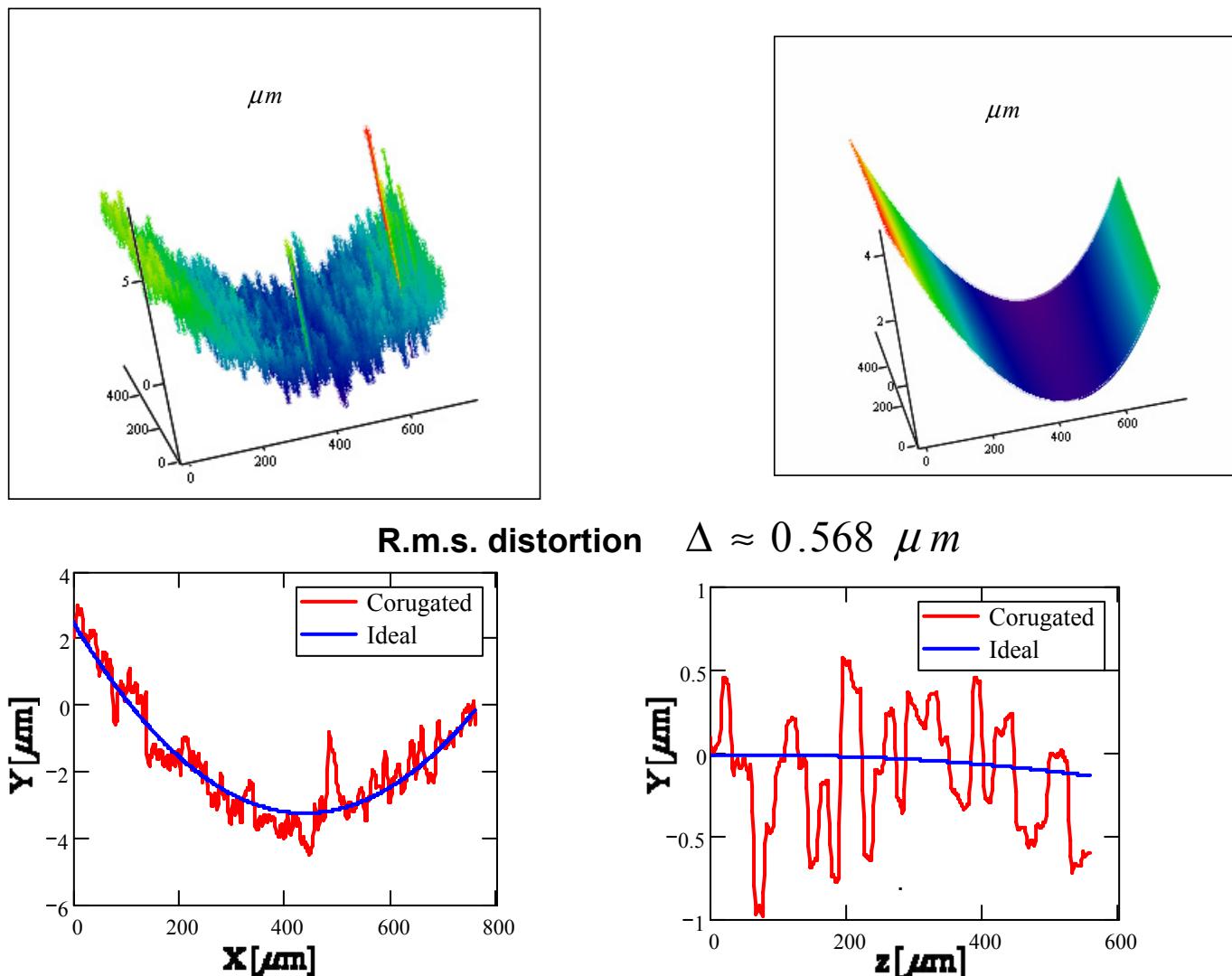


Geometrical longitudinal wake potentials of Gaussian bunch $\sigma_b = 20 \mu\text{m}$

$$E = 17.5 \text{ GeV}$$

	Entrance	Exit	Total
Loss Factor[kV / nC]	0.36	-462.39	-462.1
Energy Spread [%]	$1.12 \cdot 10^{-3}$	1.057	1.058

Surface Roughness in Undulator Section



Measurement data from T. Wohlenberg

$$Z(\omega) = \frac{Z_s(\omega)}{2\pi R} \left[1 + i \frac{\omega}{c} \frac{R}{2} \frac{Z_s(\omega)}{Z_0} \right]^{-1}$$

Surface Impedance

$$Z_s(\omega) = Z_s^\sigma(\omega) + Z_s^L(\omega) \quad \text{where}$$

Inductance define as

$$L = \frac{Z_0}{2\pi c a} \int dk_x dk_z \tilde{R}(k_x, k_z) \frac{k_z^2}{\sqrt{k_x^2 + k_z^2}}$$

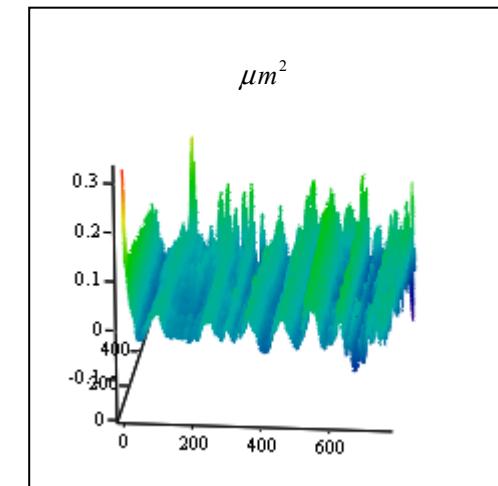
Where $\tilde{R}(k_x, k_z)$ is *spectral density* defined as Fourier Transformation of *Autocorrelation* function:

$$R(x, z) = \frac{1}{A(x, z)} \int_{A(x, z)} [\delta r(\hat{x}, \hat{z}) \delta r(\hat{x} - x, \hat{z} - z)] d\hat{x} d\hat{z}$$

$$\sigma = 58 \times 10^6 \Omega^{-1} m^{-1}$$

$$R = 4.4 \text{ mm}$$

$$Z_s^\sigma(\omega) \approx \sqrt{\frac{i\omega\mu}{\sigma(\omega)}} \\ Z_s^L(\omega) \approx i\omega L$$

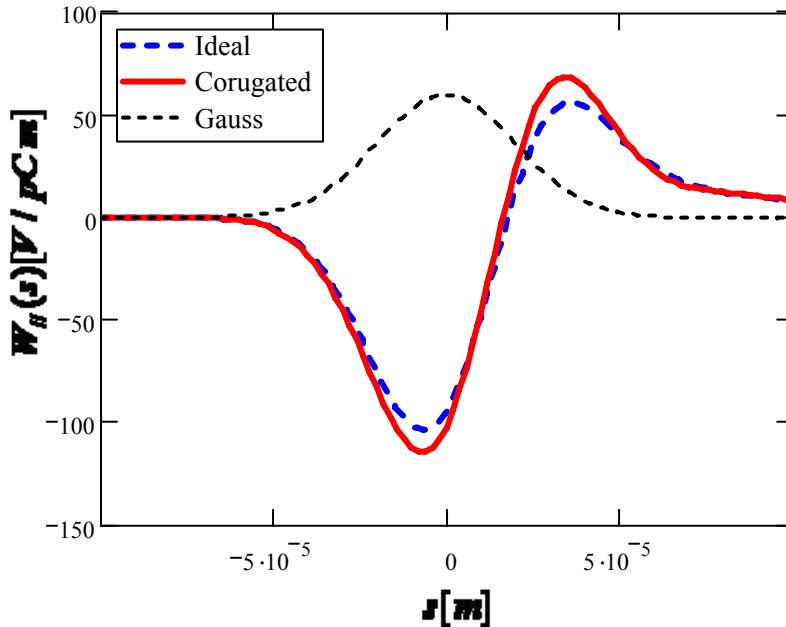


G.V.Stupakov, SLAC-PUB-8208, 1999

M.Dohlus, M.I. Ivanyan, V.M. Tsakanov, TESLA-FEL 2000-26,2000

M.Dohlus. TESLA 2001-26, 2001

Wake Potential of Corrugated pipe



	Ideal	Corrugated
Loss Factor [kV / nC]	-50.698	-52.703
Energy Spread [%]	0.286	0.33

R.m.s. value of the roughness in μm

	AL_AU	AL_CU	AL_ELP	AL_UNB	AL_GEB
Meas. 1	0.568	0.371	0.395	0.567	2.835
Meas. 2	0.547	0.745	0.360	0.520	-----
Meas. 3	0.514	0.418	0.346	0.457	-----

Arithmetical Mean Roughness Ra [μm]

	AL_AU	AL_CU	AL_ELP	AL_UNB	AL_GEB
Meas. 1	0.425	0.288	0.312	0.463	2.202
Meas. 2	0.430	0.362	0.285	0.418	-----
Meas. 3	0.410	0.333	0.274	0.356	-----

Abbreviations

AU	Gold
CU	Copper
ELP	Electro polish
UNB	Untreated (Unbehandelt)
GEB	Etched (Gebeizt)

Summary

- Impedance Structure for Ceramic Kicker Vacuum Chamber was Investigated. For Kicker was shown that Wake Potential for two layer tube can be estimated by single layer tube formula.
- Was analyzed the transition Wakes influence on the beam.
- Influence of surface corrugation in Undulator vacuum chamber on the beam was calculated.

Acknowledgements:

Thanks to Martin Dohlus, I. Zagorodnov, T. Wohlenberg, M. Ivanyan and V. Tsakanov for stimulating discussions.